

ABSTRACT OF THE DISCLOSURE

There is disclosed an inner circuit constituted of a high voltage-proof circuit section and a low voltage-proof circuit section. A usual protective circuit  
5 against a surge is directly connected to an external terminal of an IC outside the inner circuit. The high voltage-proof circuit section includes a MOS transistor driven by a power voltage VDD. The low voltage-proof circuit section includes a MOS transistor driven by  
10 a power voltage Vdd lower than the power voltage VDD. The protective circuit against the surge is individually connected to the MOS transistor driven by the power voltage Vdd. A capacitor, diode, and the like are used as the protective circuit.